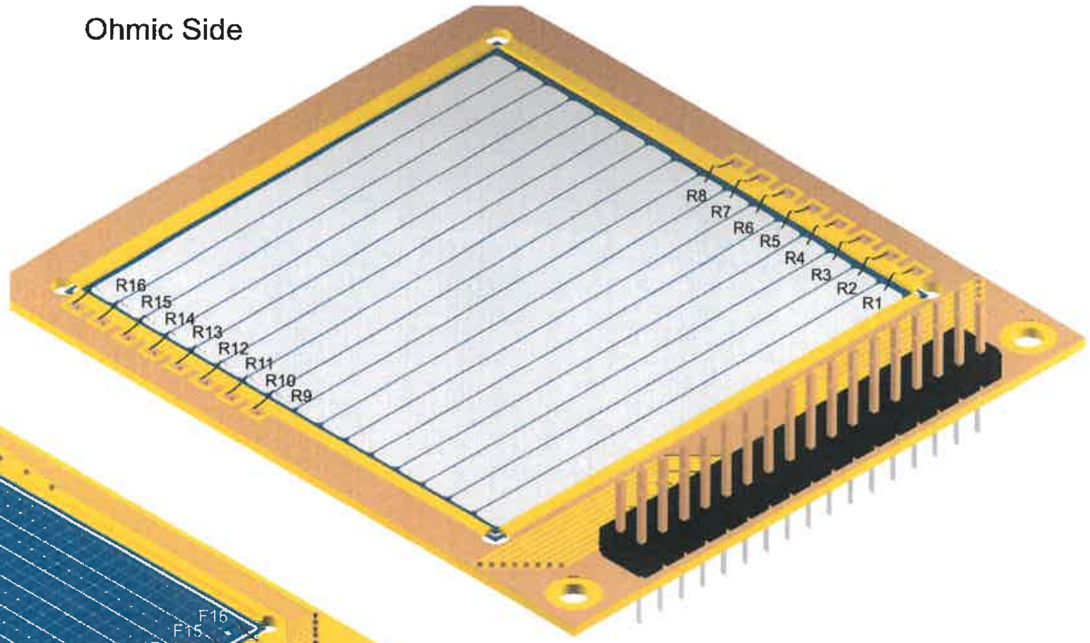
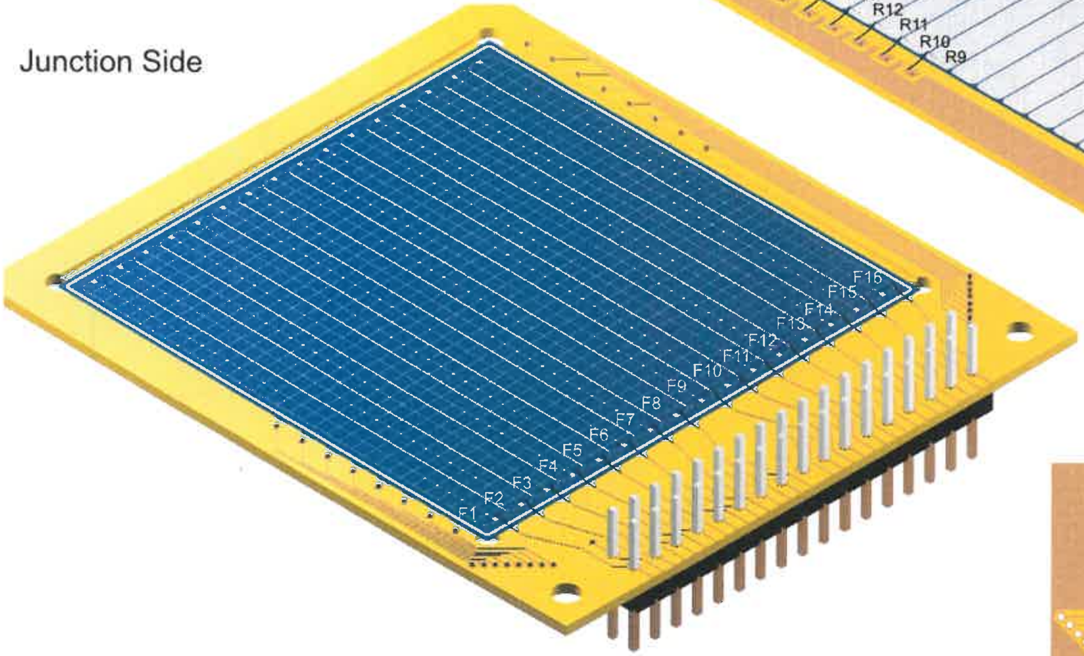
Drg. No A-3961

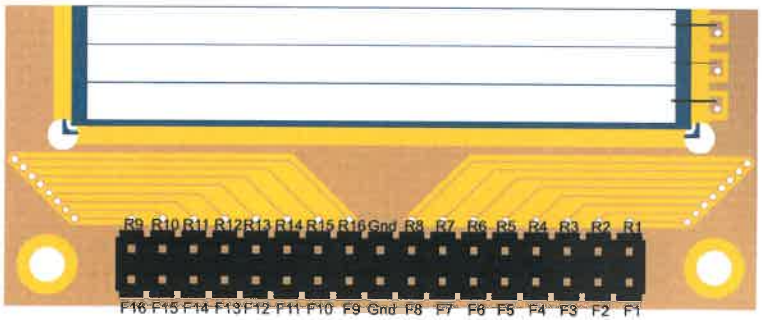
Ohmic Side



Junction Side



Connector Outputs (viewed from rear)



PCB Dimensions = 61.5 x 71.0 mm
Detector Dimensions = 54.4 x 54.4 mm
Active Area = 50.0 x 50.0 mm

Drawn N.W	Checked S.W	Date 21/07/2011	Tolerances Unless Stated	Outputs Via: Samtec Part number TSW-117-08-L-D
Des. Appd. Micron			Package O/D ± 0.1 mm	Mating connector: Samtec SSW, SSQ, SSM, ESW, ESQ, BCS, BSW, CES, SLW, IDSD, IDSS series
			Package Hole ± 0.05 mm	Potted Wire Bonds: No
			Package Hole Pos'n ± 0.1 mm	Substrate Number: A-2961
			Detector O/D ± 20.0 µm	Substrate Material: 3.2 mm thick FR4 PCB Material
				Connector Orientation: To exit rear of PCB.

Title.

Design W1 (DS) Type 9G
With Straight Connector Exiting Rear
3D Assembly

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graphics@micronsemiconductor.co.uk

Scale N/A	Dims In. mm	Drg No A-3961

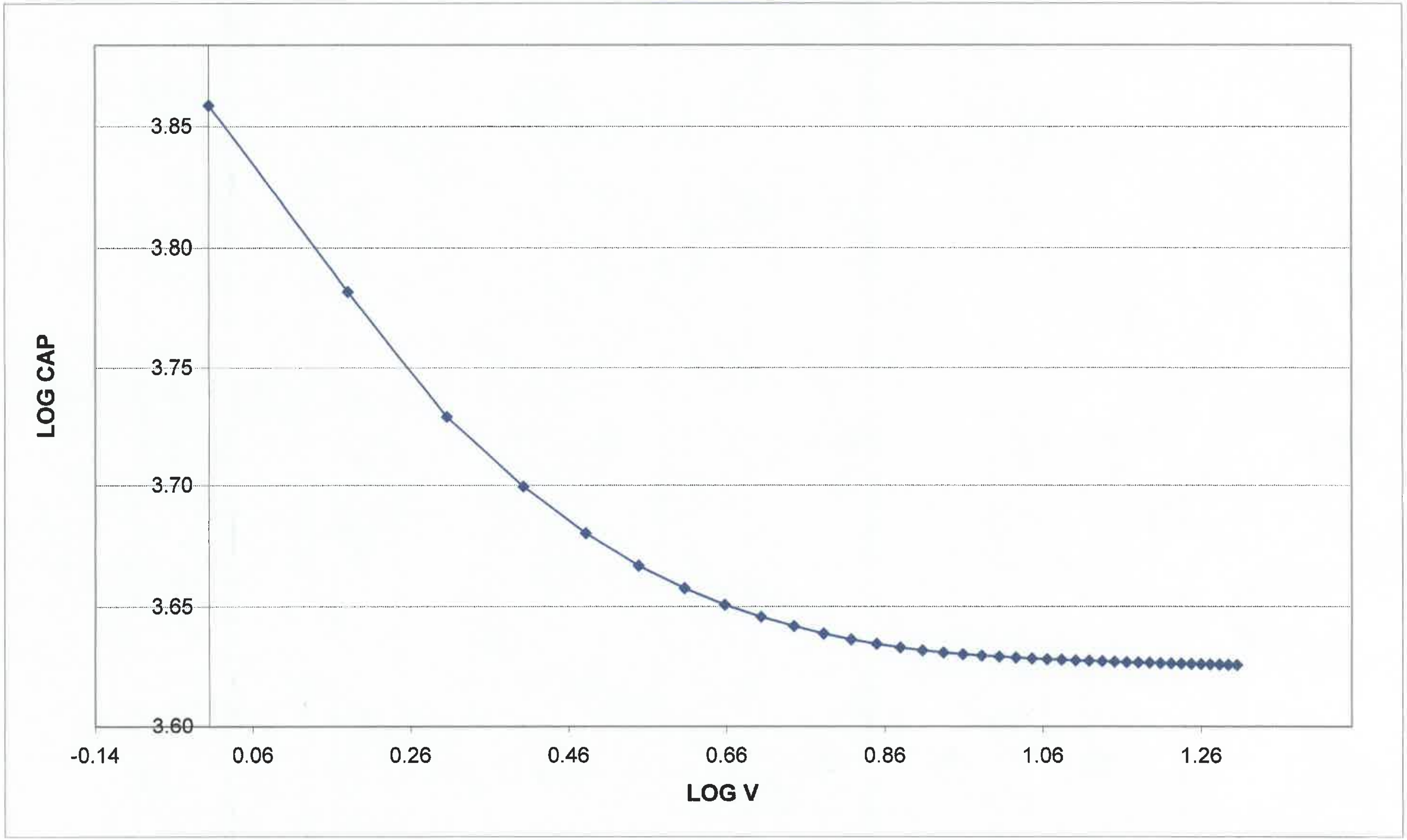
Depletion Plot

Design-W

Wafer No.: 2410-14

Thickness: 61 um

Depletion: 8.5 Volts



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19-05-15

Resolution Plot

DESIGN W1-60 TYPE 9G

Wafer No.: **2410-14**

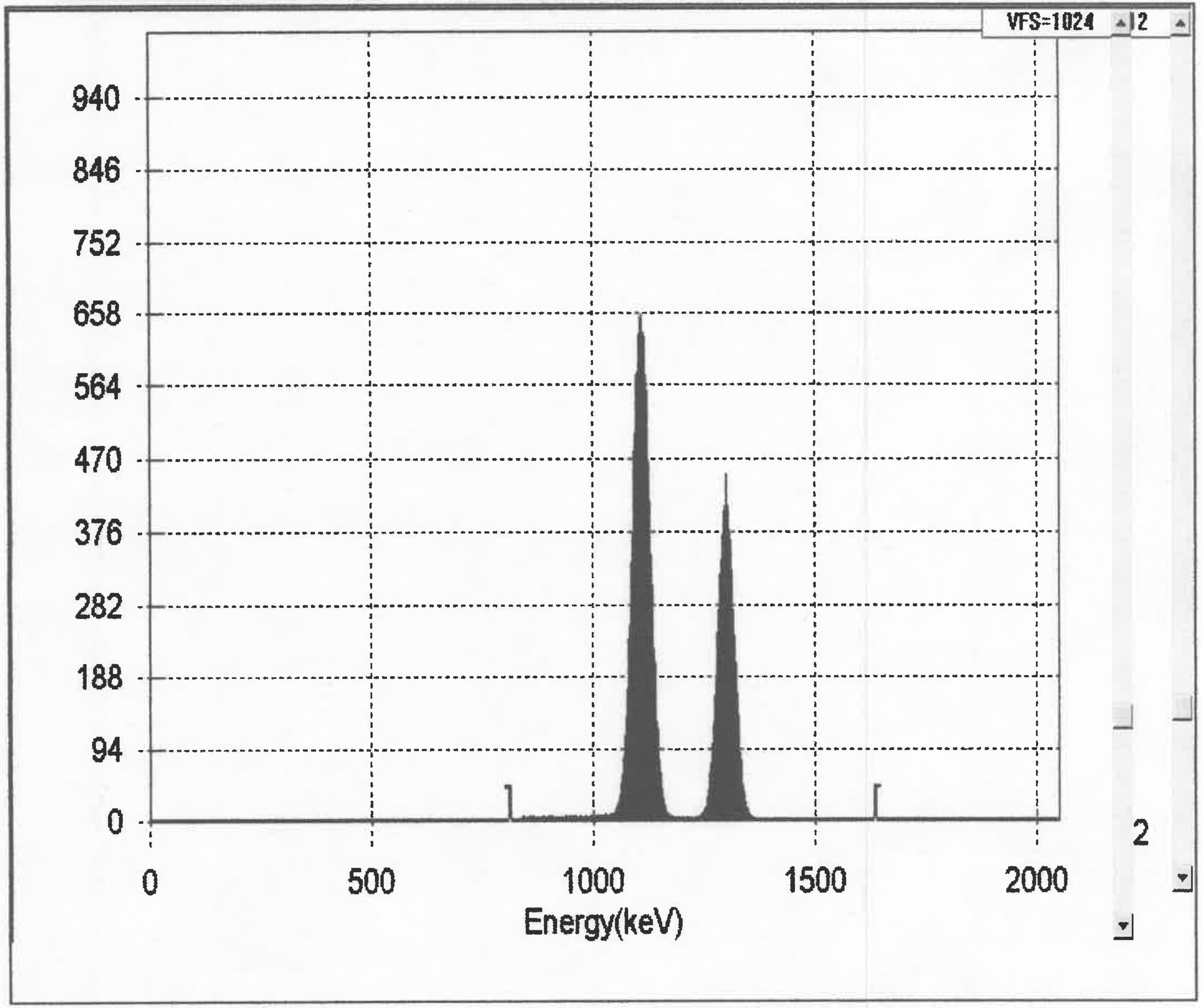
Thickness: **61** um

JUNCTION

DET LINE: 205 KeV
SYSTEM: 162 KeV
CAL: 124 KeV

OHMIC

DET LINE: 209 KeV
SYSTEM: 162 KeV
CALC: 131 KeV



Source
Am 241

Rise Time
1

Flat Top
0

T=22.1DC

BIAS VOLTS= 20 V

Leakage 150 nA

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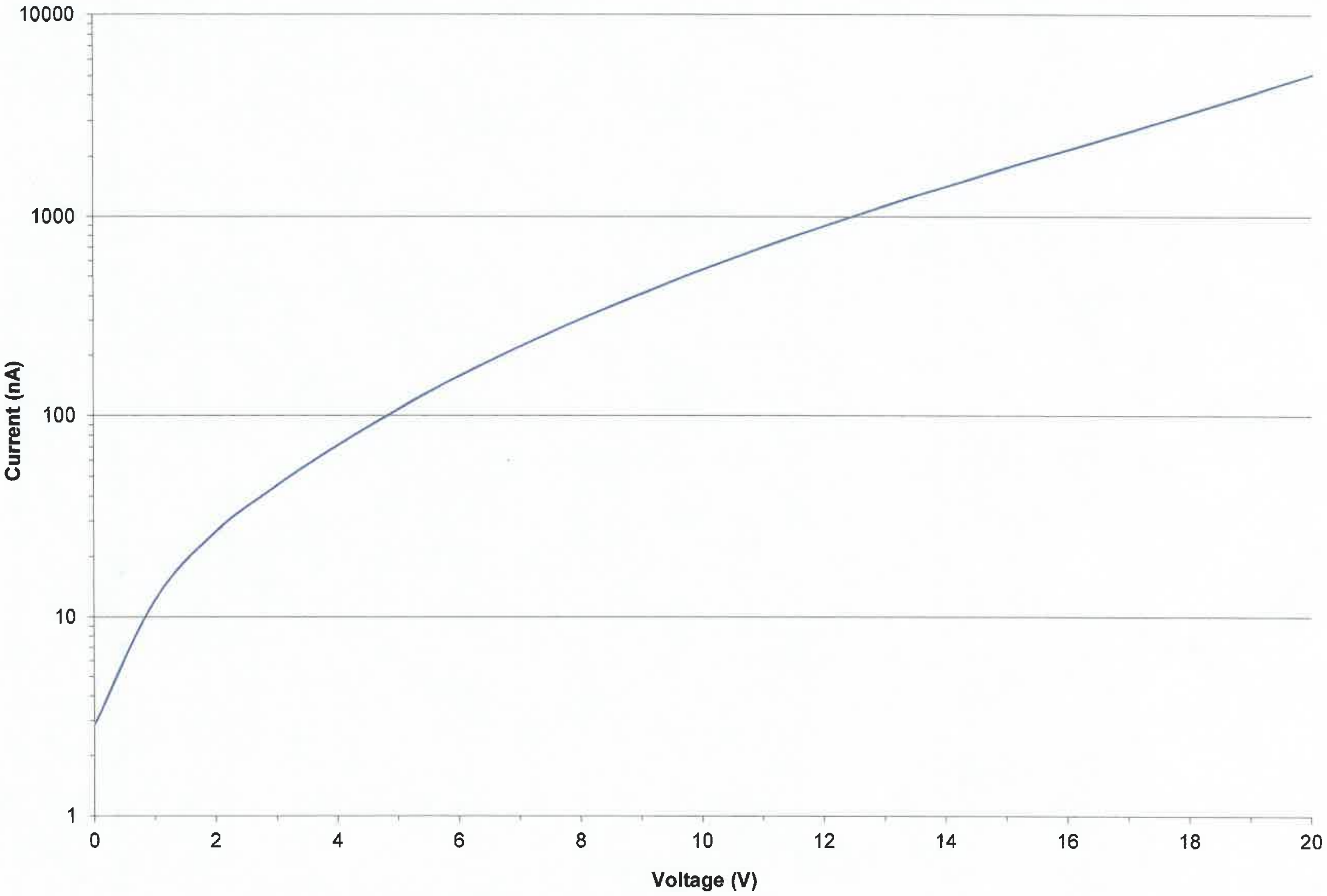
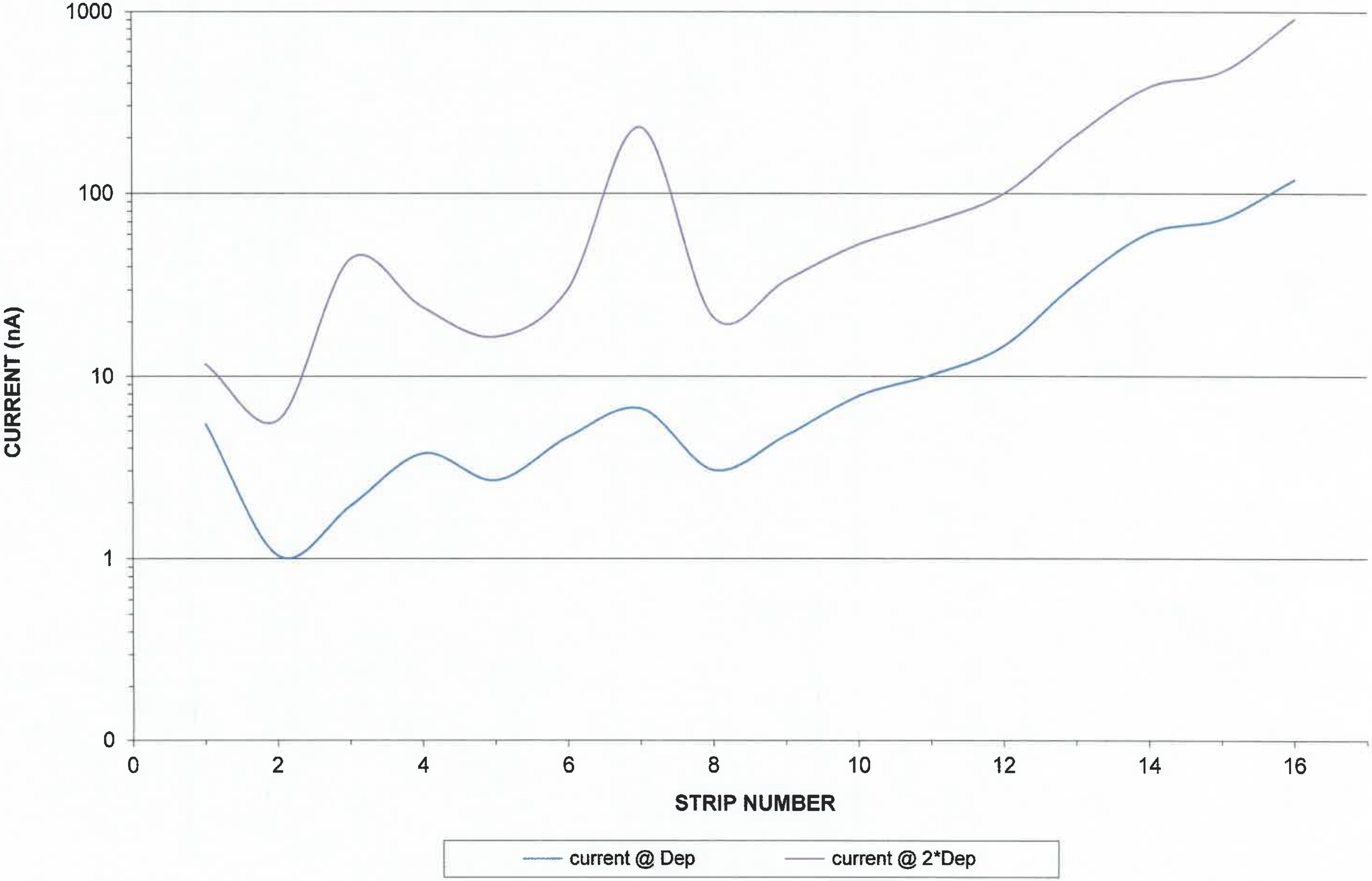
09/09/2015

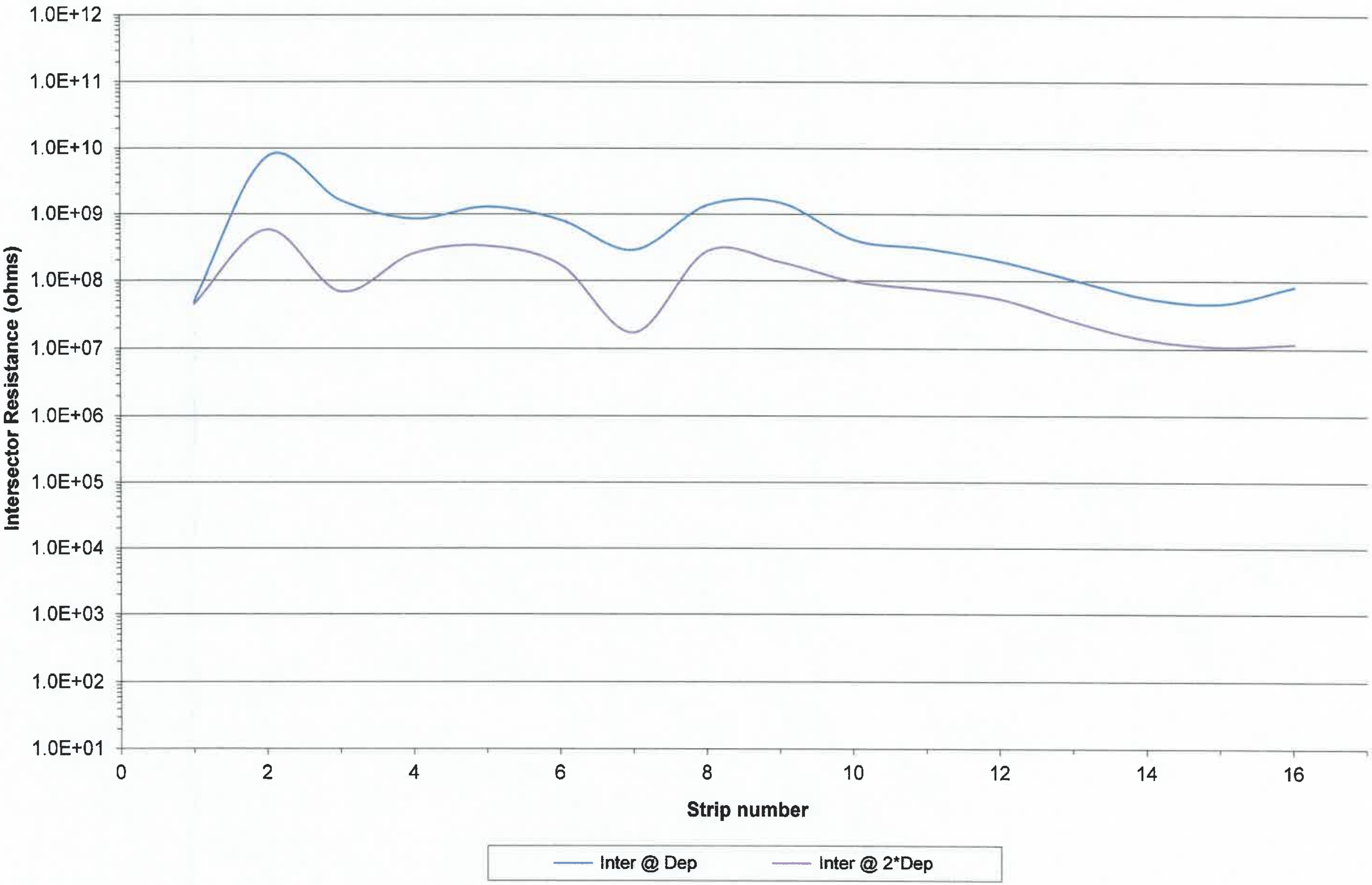
Design-W D/S
2410-14 TOTAL DETECTOR IV
Dep=8.5V Thickness=61um



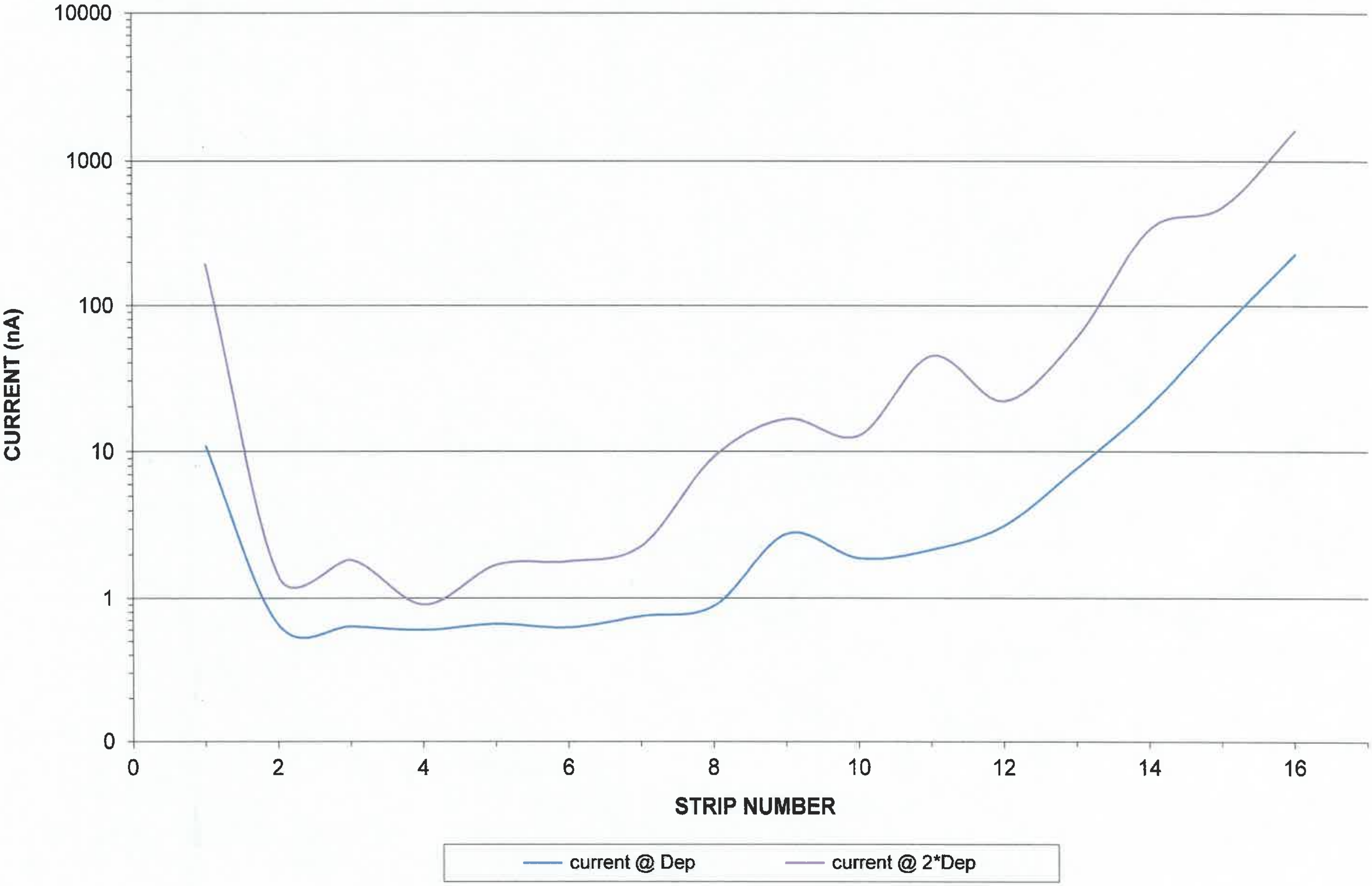
Design-W N-TYPE
2410-14 Junction side Dep=8.5V Thickness=61um

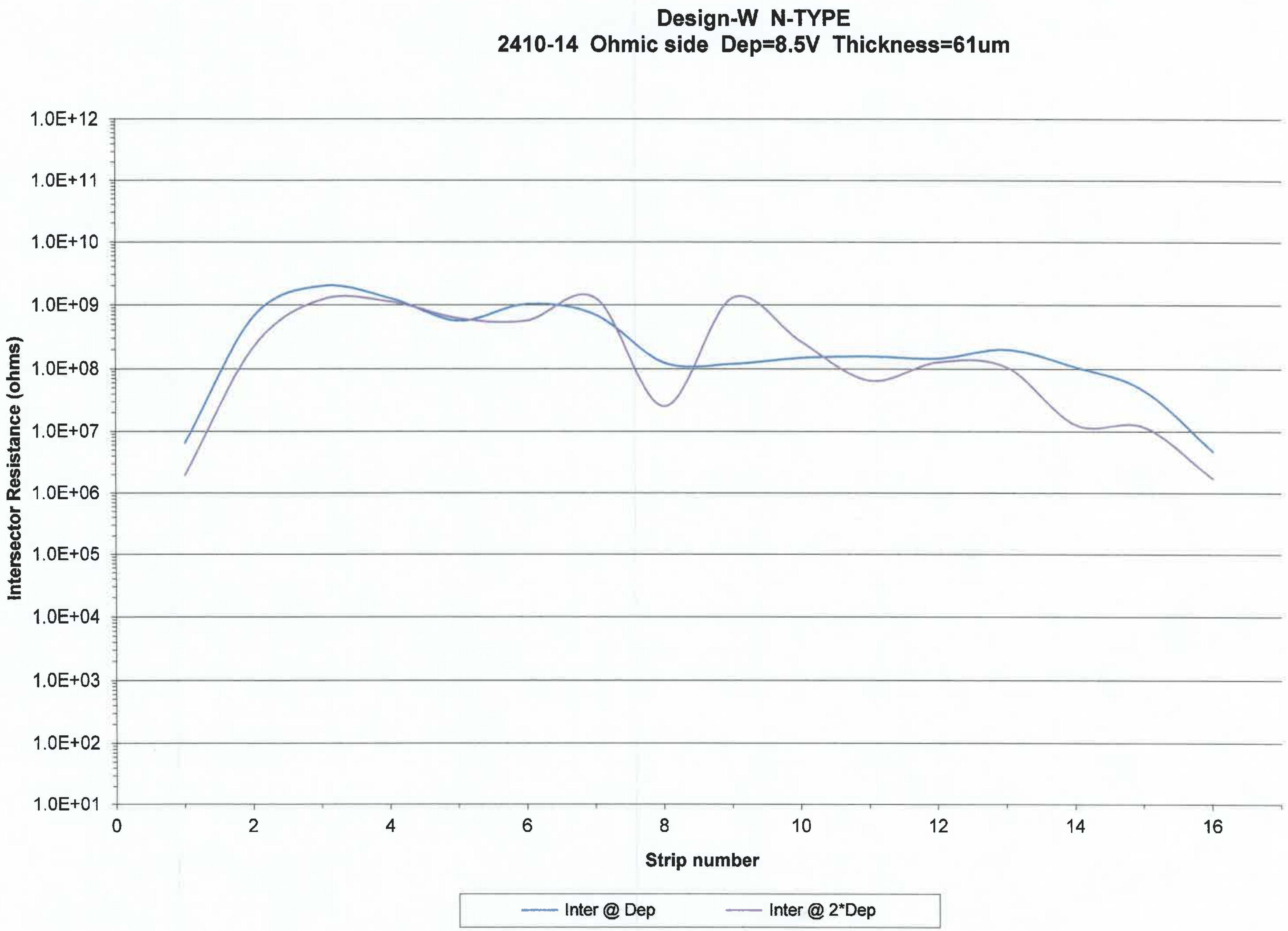


Design-W 9G/2M ceramic N-TYPE
2801-1 Junction side Dep=10V Thickness=54um



Design-W N-TYPE
2410-14 Ohmic side Dep=8.5V Thickness=61um





Design-W N-TYPE
2410-14 Ohmic side Dep=8.5V Thickness=61um